

CMLD6001

**SURFACE MOUNT
DUAL, ISOLATED
LOW LEAKAGE SILICON
SWITCHING DIODES**

PICOmini™



SOT-563 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD6001 type contains Two (2) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a PICOmini™ surface mount package. These devices are designed for switching applications requiring extremely low leakage.

MARKING CODE: C6D

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R 75
 V_{RRM} 100
 I_F 250
 I_{FSM} 4.0
 I_{FSM} 1.0
 P_D 250
 T_J, T_{stg} -65 to +150
 θ_{JA} 500

UNITS

V
V
mA
A
A
mW
 $^{\circ}\text{C}$
 $^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=75\text{V}$		500	pA
BV_R	$I_R=100\mu\text{A}$	100		V
V_F	$I_F=1.0\text{mA}$		0.85	V
V_F	$I_F=10\text{mA}$		0.95	V
V_F	$I_F=100\text{mA}$		1.1	V
C_T	$V_R=0, f=1.0\text{MHz}$		2.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\Omega$ Rec. to 1.0mA		3.0	μs

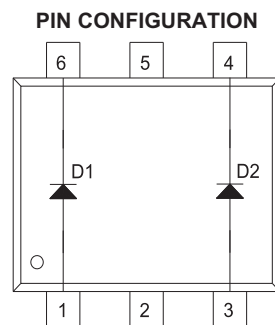
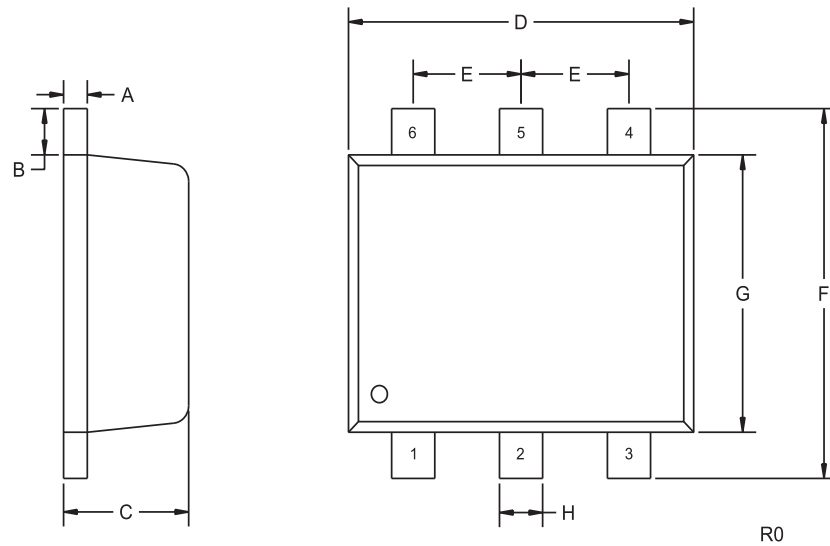
R2 (18-January 2010)

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SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Anode D2
- 4) Cathode D2
- 5) NC
- 6) Cathode D1

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